

Takeharu Kuroiwa

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Dielectric Properties of $(\text{Ba}_x\text{Sr}_{1-x})\text{TiO}_3$ Thin Films Prepared by RF Sputtering for Dynamic Random Access Memory Application. Japanese Journal of Applied Physics, 1994, 33, 5187-5191.	1.5	110
2	Dielectric Relaxation of $(\text{Ba},\text{Sr})\text{TiO}_3$ Thin Films. Japanese Journal of Applied Physics, 1995, 34, 5478-5482.	1.5	87
3	Model of leakage characteristics of $(\text{Ba},\text{Sr})\text{TiO}_3$ thin films. Applied Physics Letters, 1998, 73, 954-956.	3.3	82
4	Electric Properties of SrTiO_3 Thin Films Prepared by RF Sputtering. Japanese Journal of Applied Physics, 1992, 31, 3025-3028.	1.5	52
5	Magnetization chirality due to asymmetrical structure in Ni-Fe annular dots for high-density memory cells. Journal of Applied Physics, 2004, 95, 6714-6716.	2.5	35
6	Practical applications of SiC-MOSFETs and further developments. Semiconductor Science and Technology, 2016, 31, 034003.	2.0	30
7	Magnetically pinned ring dots for spin valve or magnetic tunnel junction memory cells. Journal of Magnetism and Magnetic Materials, 2005, 286, 31-36.	2.3	21
8	Preparation of $\text{Bi}_{3.25+x}\text{La}_{0.75}\text{Ti}_3\text{O}_{12+y}$ Films on Ruthenium Electrodes. Japanese Journal of Applied Physics, 2002, 41, 2105-2109.	1.5	14
9	Effects of Oxygen Vacancy Diffusion on Leakage Characteristics of $\text{Pt}/(\text{Ba}_{0.5}\text{Sr}_{0.5})\text{TiO}_3/\text{Pt}$ Capacitor. Japanese Journal of Applied Physics, 2000, 39, L416-L419.	1.5	12
10	Influence of Buffer Layers and Barrier Metals on Properties of $(\text{Ba},\text{Sr})\text{TiO}_3$ Films Prepared by Liquid Source Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1997, 36, 5874-5878.	1.5	10
11	Improved fabrication process for Ru/BST/Ru capacitor by liquid source chemical vapor deposition. Thin Solid Films, 2002, 409, 8-14.	1.8	9
12	Demonstration of High Quality 4H-SiC Epitaxial Growth with Extremely Low Basal Plane Dislocation Density. Materials Science Forum, 0, 778-780, 91-94.	0.3	9
13	Properties of a SiC Schottky Barrier Diode Fabricated with a Thin Substrate. Materials Science Forum, 0, 778-780, 820-823.	0.3	7
14	Suppression of Switching-Field Variation by Surface Oxidation Depending on the Shape of the CoFeB Free Layer. IEEE Transactions on Magnetics, 2007, 43, 2352-2354.	2.1	5
15	Fatigueless Ferroelectric Capacitors with Ruthenium Bottom and Top Electrodes Formed by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2005, 44, L378-L380.	1.5	4
16	Evaluation of distribution of exchange coupling in CoFe/Ru/CoFe synthetic antiferromagnetic structure after annealing. Journal of Applied Physics, 2009, 105, .	2.5	4
17	Demonstration of High Quality 4H-SiC Epitaxy by Using the Two-Step Growth Method. Materials Science Forum, 0, 778-780, 167-170.	0.3	4
18	Influence of Growth Pressure and Addition of HCl Gas on Growth Rate of 4H-SiC Epitaxy. Materials Science Forum, 2015, 821-823, 133-136.	0.3	4

#	ARTICLE	IF	CITATIONS
19	Transition between onion states and vortex states in exchange-coupled Ni ²⁺ /Fe ³⁺ /Mn ²⁺ /Ir asymmetric ring dots. Journal of Applied Physics, 2006, 99, 08G303.	2.5	3
20	Thermal robustness in synthetic antiferromagnetic free layer for magnetic random access memory applications. Journal of Applied Physics, 2006, 99, 08C911.	2.5	3
21	Determination of Structure Factors of Al ₂ O ₃ by means of Large Angle Convergent Beam Electron Diffraction. Materials Transactions, JIM, 1995, 36, 1344-1348.	0.9	2
22	Novel stacked capacitor technology for 1-Gbit DRAMs with (Ba,Sr)TiO ₃ thin films. Electronics and Communications in Japan, 1997, 80, 70-78.	0.2	2
23	Chemical Vapor Deposition of Ru Bottom Electrode for Ferroelectric Bi _{4-x} La _x Ti ₃ O ₁₂ Capacitors. Integrated Ferroelectrics, 2003, 59, 1437-1443.	0.7	2
24	Magnetization Chirality of Ni-Fe and Ni-Fe/Mn-Ir Asymmetric Ring Dots for High-Density Memory Cells. Materials Science Forum, 2006, 512, 171-176.	0.3	2
25	Control of pinned layer magnetization direction in spin-valve-type magnetic tunnel junction with an IrMn layer. Journal of Applied Physics, 2004, 95, 6795-6797.	2.5	1
26	High-temperature operations of rotation angle sensors with spin-valve-type magnetic tunnel junctions. IEEE Transactions on Magnetics, 2005, 41, 3628-3630.	2.1	1
27	Leakage current characteristics of Pt ²⁺ /Bi _{4-x} La _x Ti ₃ O ₁₂ /Ru ferroelectric capacitors fabricated on metal-organic chemical vapor deposited Ru films. Journal of Applied Physics, 2006, 100, 014108.	2.5	1
28	Chemical Vapor Deposition of Ru Bottom Electrode for Ferroelectric Bi _{4-x} La _x Ti ₃ O ₁₂ Capacitors. Integrated Ferroelectrics, 2003, 59, 1437-1443.	0.7	0
29	Read-Cycle Endurance of Magnetic Random Access Memory Elements. IEEE Transactions on Magnetics, 2004, 40, 2631-2633.	2.1	0
30	Characteristics of a Schottky Barrier Diode and the SiC Wafers Sliced by Wire Electrical Discharge Machining. Materials Science Forum, 0, 778-780, 784-787.	0.3	0